Complementary Silicon Plastic Power Transistors

Designed for use in general purpose amplifier and switching applications.

Features

- High Current Gain Bandwidth Product
- Compact TO-220 AB Package
- Epoxy Meets UL94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

| Rating | Symbol | BD242B | BD241C BD242C | Unit |
|--|-----------------------------------|-------------|------------------|-----------|
| Collector-Emitter Voltage | V _{CEO} | 80 | 100 | Vdc |
| Collector-Emitter Voltage | V _{CES} | 90 | 115 | Vdc |
| Emitter-Base Voltage | V_{EB} | 5.0 | | Vdc |
| Collector Current –Continuous | ۱ _C | 3.0 | | Adc |
| Collector Current – Peak | I _{CM} | 5.0 | | Adc |
| Base Current | Ι _Β | 1.0 | | Adc |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | P _D | 40 0.32 | | W W/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +150 | | °C |
| ESD – Human Body Model | HBM | 3 | В | V |
| ESD – Machine Model | MM | (|) | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Мах | Unit | |
|---|-----------------|-------|------|--|
| Thermal Resistance, Junction-to-Ambient | R_{\thetaJA} | 62.5 | °C/W | |
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 3.125 | °C/W | |

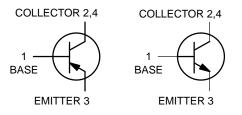


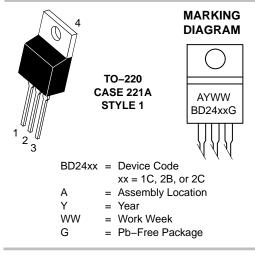
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ORDERING INFORMATION

| Device | Package | Shipping [†] |
|---------|---------------------|-----------------------|
| BD241CG | TO-220 (Pb-Free) | 50 Units/Rail |
| BD242BG | TO-220 (Pb-Free) | 50 Units/Rail |
| BD242CG | TO-220 (Pb-Free) | 50 Units/Rail |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

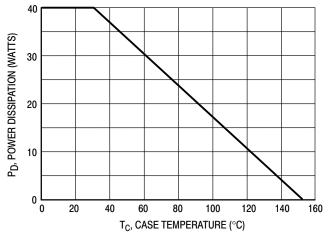
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit | | | | |
|---|--------------------------|----------------------|-----------|------|------|--|--|--|
| OFF CHARACTERISTICS | | | | | | | | |
| Collector–Emitter Sustaining Voltage (Note 1) $(I_C = 30 \text{ mAdc}, I_B = 0)$ | BD242B BD241C, BD242C | V _{CEO} | 80 100 | | Vdc | | | |
| Collector Cutoff Current $(V_{CE} = 50 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$ | BD242B BD241C, BD242C | I _{CEO} | | 0.3 | mAdc | | | |
| Collector Cutoff Current ($V_{CE} = 80 \text{ Vdc}, V_{EB} = 0$) ($V_{CE} = 100 \text{ Vdc}, V_{EB} = 0$) | BD242B BD241C, BD242C | I _{CES} | | 200 | μAdc | | | |
| Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$) | | I _{EBO} | | 1.0 | mAdc | | | |
| ON CHARACTERISTICS (Note 1) | | | | | | | | |
| DC Current Gain (I _C = 1.0 Adc, V _{CE} = 4.0 Vdc) (I _C = 3.0 Adc, V _{CE} = 4.0 Vdc) | | h _{FE} | 25 10 | | | | | |
| Collector–Emitter Saturation Voltage $(I_C = 3.0 \text{ Adc}, I_B = 0.6 \text{ Adc})$ | | V _{CE(sat)} | | 1.2 | Vdc | | | |
| Base–Emitter On Voltage ($I_C = 3.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$) | | V _{BE(on)} | | 1.8 | Vdc | | | |
| DYNAMIC CHARACTERISTICS | | | | | | | | |
| Current Gain – Bandwidth Product (Note 2) ($I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f_{test} = 1.0 \text{ MHz}$) | | f _T | 3.0 | | MHz | | | |
| Small–Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz) | | h _{fe} | 20 | | | | | |

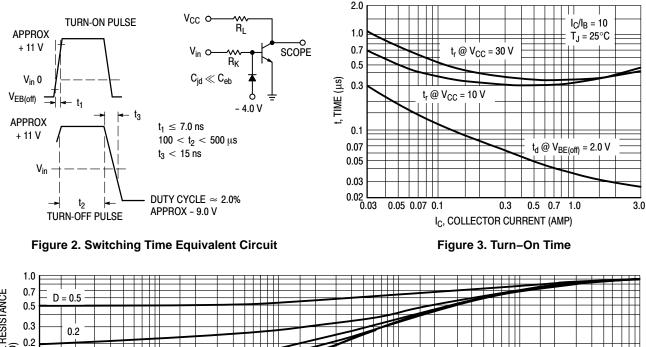
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

2. $f_T = |h_{fe}| \bullet f_{test}$.







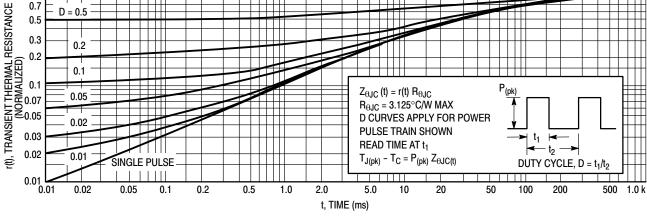
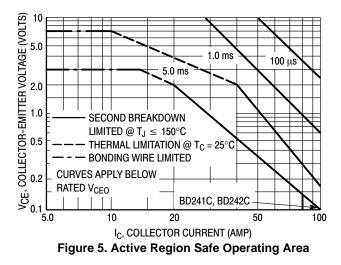
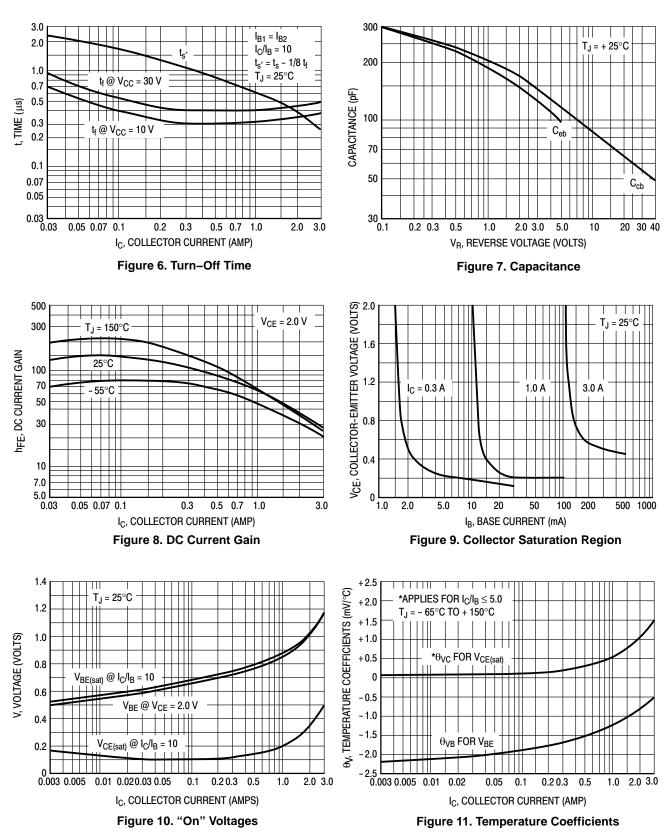


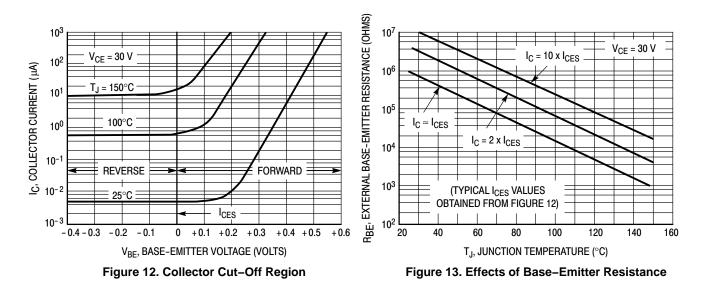
Figure 4. Thermal Response



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}$ C; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}$ C, $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.





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